

IN THE CLAIMS

Please amend the claims as follows:

Claims 1-9 (Canceled).

Claim 10 (Currently Amended): A method according to claim ~~[[17]]~~ 18, wherein the fastening includes a bonding chosen from bonding by molecular adhesion via intermediate films or without intermediate films, bonding by reaction, metallic bonding, brazing or bonding by species diffusion.

Claim 11 (Currently Amended): A method according to claim ~~[[17]]~~ 18, further comprising healing annealing of the implantation defects on the thin film.

Claim 12 (Currently Amended): A method according to claim 11, wherein the healing annealing is carried out before the thinning ~~down the thin film~~.

Claim 13 (Currently Amended): A method according to claim 11, wherein the healing annealing is carried out after the thinning ~~down the thin film~~.

Claims 14-17 (Canceled).

Claim 18 (New): A method for transferring an electrically active SiC thin layer from an initial SiC substrate, the method comprising:

determining hydrogen ion implantation conditions including dose, energy and implantation current that create a buried, embrittled film at a depth, with respect to an implanted face of the initial SiC substrate, wherein an implantation defect concentration in a

first 500 nm of implanted SiC is lower than 9.10^{20} atoms/cm³, and a number of acceptor defects compatible with desired electrical properties of an active thin layer is obtained;

performing hydrogen ion implantation through a face of the initial SiC substrate, under said determined hydrogen ion implantation conditions, and creating said buried, embrittled film;

fastening the face of the initial SiC substrate after implantation to a face of a target substrate, to obtain a structure;

separating the structure in two parts at a level of the buried embrittled film; and

thinning a layer of the SiC remaining fastened to the target substrate to a thickness lower than 500 nm.